

Accordingly, Applicant courteously requests entry of the following amendment.

In the Specification:

Page 1, between lines 6 and 7 insert: **–BACKGROUND OF THE INVENTION.**

1. Field of the Invention.--

line 8: after "and" insert **–to–** and after "processing" insert **–a–**;

between lines 12 and 13: insert **–2. The Prior Art.–**;

line 23: change "be" to **–by–**;

page 2, line 18: change "during" to **–along–**; ¹⁾

page 3, line 25: change "step" to **–steps–**;

page 4, line 1: after "strength" insert **–between–**;

line 15: change "beginnings" to **–approach to–**;

line 16: change "of an irradiation of" to **–irradiating**;

page 5, between lines 10 and 11: insert **–OBJECT OF THE INVENTION.–**

between lines 16 and 17: insert **–BRIEF SUMMARY OF THE INVENTION.–**;

lines 19 to 21: cancel and substitute therefor **–bombardment of a solid material carrier foil by high energy heavy ion irradiation at two different angles and under special controlled conditions, hereafter to be described, so as initially to form in the carrier foil intersecting ion traces which by subsequent chemical etching form intersecting channels below the surface of the carrier foil for securely anchoring a metal layer precipitated on the surface of the carrier foil.**

Other objects will in part be obvious and will in part appear hereinafter.–;

page 6, line 2: change "of" (first occurrence) to **–in–**;

line 17: change "Waal" to **–Waals–**; ²⁾

page 7, line 19: change "be" to **–been–**;

page 8, line 17: change "intersection" to **–intersections–**;

¹⁾ "during" refers to time; but since a trajectory is something occurring in space rather than time, the adjective **–along–** is deemed to be appropriate.

²⁾ The (Dutch) physicist's surname was **–van der Waals–** not "van der Waal".

page 10, lines 12 to 17: cancel and substitute therefor --DESCRIPTION OF THE SEVERAL DRAWINGS.

The novel features which are considered to be characteristic of the invention are set forth with particularity in the appended claims. The invention itself, however, in respect of its structure, construction and lay-out, as well as manufacturing techniques, together with other objects and advantages thereof, will be best understood from the following description when read with reference to the drawings, in which:--

page 11, line 3: enter --DETAILED DESCRIPTION OF THE PREFERRED EMBODIMENT.--;

page 22: cancel lines 1 - 11 and substitute therefor --ABSTRACT OF THE DISCLOSURE.

A method of an system for improving the strength of connection between a carrier substrate and a cover layer by obliquely bombarding the substrate at least one of its surfaces with heavy ion irradiation from two different angles to produce intersecting ion traces therein which by subsequent chemical etching are formed into intersecting recesses wherein a precipitated cover layer may be anchored.--

In the claims:

Please rewrite claim 20 as follows:

20. (Currently amended) A method of processing a surface of a dielectric carrier material to adapt it for securely attaching thereto a cover layer by precipitation, comprising the steps of:

irradiating the surface at predetermined influx angles by at least one beam of high energy heavy ions of predetermined density and energy dissipation to generate within the carrier material a first plurality of latent ion traces extending into the carrier material to a predetermined depth and at a predetermined influx angle and a second plurality of latent ion traces substantially similar to and intersecting the latent ion traces of the first plurality;

selectively decelerating the heavy ions for preventing the permeation thereof through the dielectric carrier material; and